

ABSTRACT OF THE DISCLOSURE

A method for aperturing a vertical-cavity surface-emitting laser (VCSEL), for increasing the external quantum efficiency and decreasing the threshold current, involves an etching mixture that is applied to the active region of the VCSEL. The etching mixture is designed in a manner to selectively etch the active region of the VCSEL at a rate substantially faster than the etch rate of at least one of the multiple DBRS associated with the VCSEL.